In the Claims:

Please enter the following amended claims 1, 5-8, 12, 14, 15 and 18-20:

1. (Once amended) A structure comprising:

a semiconductor die having a source bond pad and a destination bond pad attached to a top surface of said semiconductor die;

a stud bump, said stud bump being situated on said destination bond pad;

a bonding wire providing a connection between said source bond pad and said stud bump, said bonding wire having an inductance defined by at least a first selected dimension of said bonding wire, wherein said first selected dimension is measured along a first axis substantially perpendicular to said top surface of said semiconductor die.

5. (Once amended) The structure of claim 1 wherein said source bond pad is not used to establish an electrical connection between said semiconductor die and a substrate, and wherein said destination bond pad is not used to establish an electrical connection between said semiconductor die and a substrate.

6. (Once amended) The structure of claim 1 wherein said inductance is further defined by at least a second selected dimension of said bonding wire, wherein said second selected dimension is measured along a second axis substantially parallel to said top surface of said semiconductor die.

7. (Once amended) The structure of claim 1 wherein said inductance is increased by increasing said first selected dimension of said bonding wire, and wherein said inductance is decreased by decreasing said first selected dimension of said bonding wire.

8. (Once amended) A structure comprising:

a semiconductor die having a first semiconductor die bond pad, a second semiconductor die bond pad, and a third semiconductor die bond pad attached to a top surface of said semiconductor die;

a first conductor providing a connection between said first semiconductor die bond pad and said second semiconductor die bond pad;

a bonding wire providing a connection between said second semiconductor die bond pad and said third semiconductor die bond pad, said bonding wire having an inductance defined by at least a selected dimension of said bonding wire, wherein said selected dimension is measured along an axis substantially perpendicular to said top surface of said semiconductor die.

12. (Once amended) The structure of claim 8 wherein said first, second, and third semiconductor die bond pads are not used to establish an electrical connection between said semiconductor die and a substrate.

14. (Once amended) The structure of claim 8 wherein said inductance is increased by increasing a said selected dimension of said bonding wire, and wherein said inductance is decreased by decreasing said selected dimension of said bonding wire.

15. (Once amended) A method for fabricating an inductor, said method comprising steps of:

fabricating a source bond pad and a destination bond pad on a top surface of a semiconductor die;

forming a stud bump on said destination bond pad;

bonding a first end of a bonding wire to said source bond pad;

bonding a second end of said bonding wire to said stud bump;

said source bond pad being a first terminal of said inductor and said destination bond pad being a second terminal of said inductor, said inductor having an inductance defined by at least a first selected dimension of said bonding wire, wherein said first selected dimension is measured along a first axis substantially perpendicular to said top surface of said semiconductor die.

18. (Once amended) The method of claim 15 wherein said source bond pad is not used to establish an electrical connection between said semiconductor die and a substrate, and wherein said destination bond pad is not used to establish an electrical connection between said semiconductor die and a substrate.

19. (Once amended) The method of claim 15 wherein said inductance is further defined by at least a second selected dimension of said bonding wire, wherein said second selected dimension is measured along a second axis substantially parallel to said top surface of said semiconductor die.

20. (Once amended) The method of claim 15 wherein said inductance is increased by increasing a said first selected dimension of said bonding wire, and wherein said inductance is decreased by decreasing said first selected dimension of said bonding wire.